



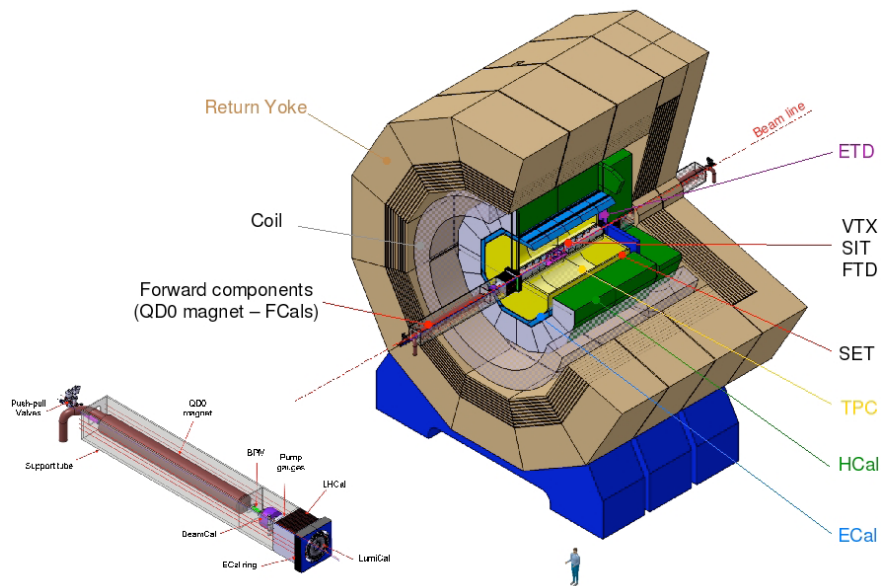
Si-W ECAL for EUDET Silicon Sensors

Rémi Cornat

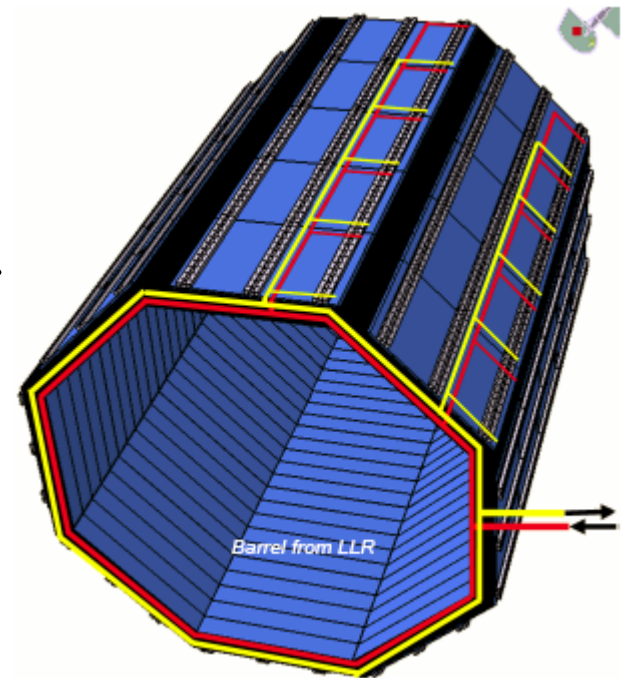


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ILD concept detector



Orienté “particle flow”
 Détecteurs à l’intérieur du solénoïde

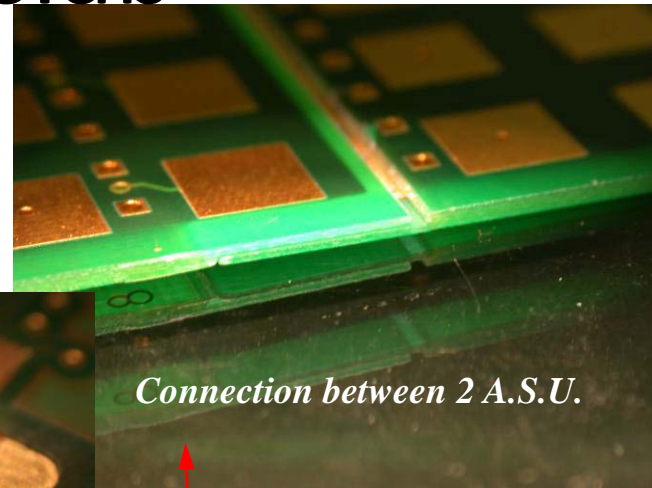


« Imaging calorimetry »
 10000 voies / dm³

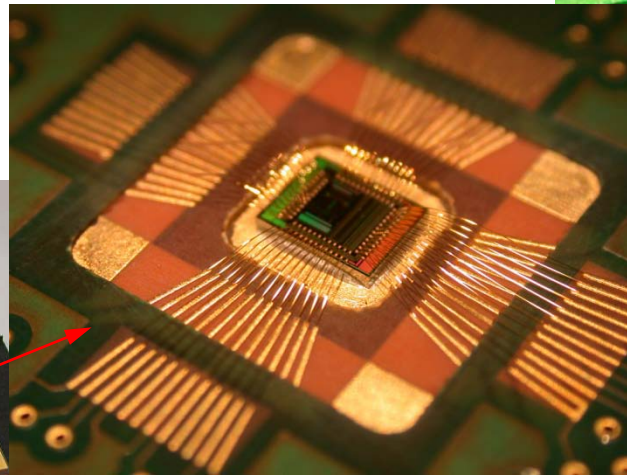
ECAL detector slab



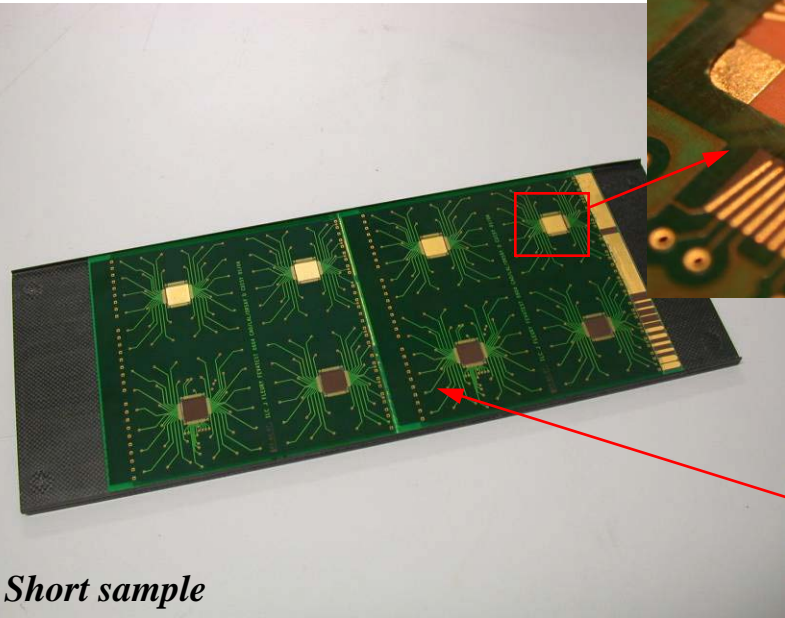
Slightly relaxed
 mechanical constraints :
 ILD + 0.4 mm



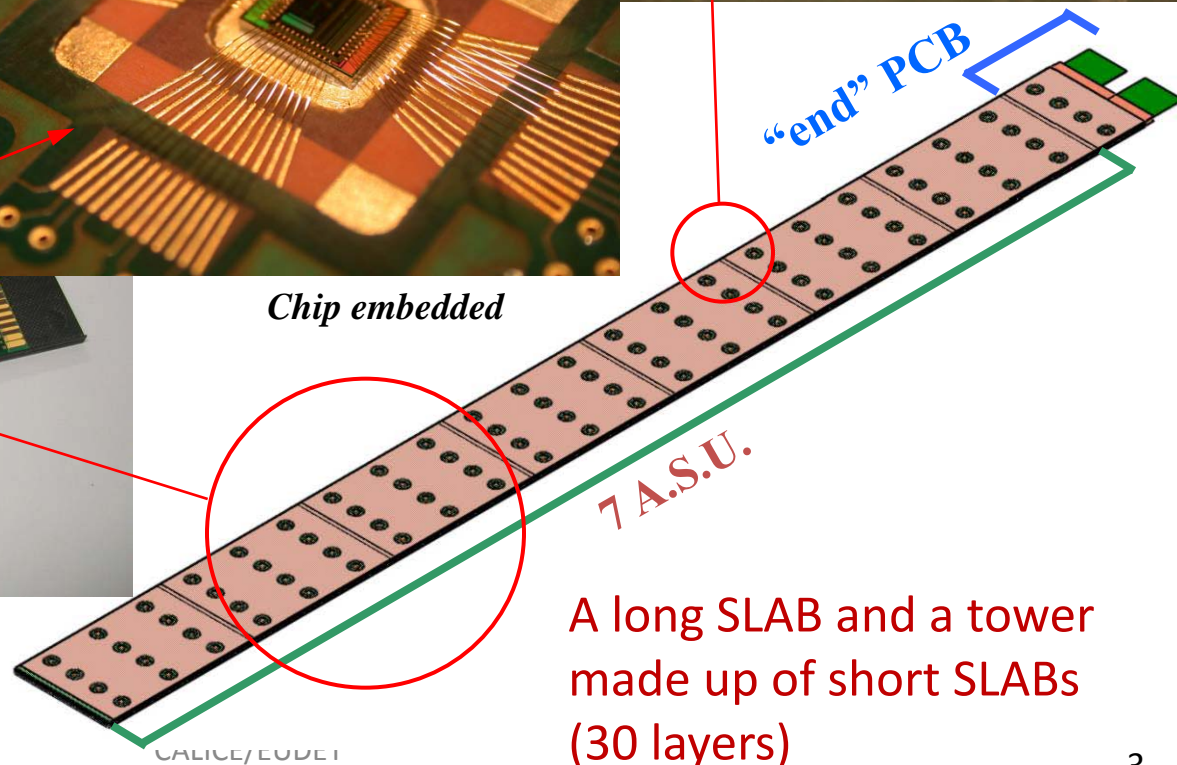
Connection between 2 A.S.U.



Chip embedded



Short sample

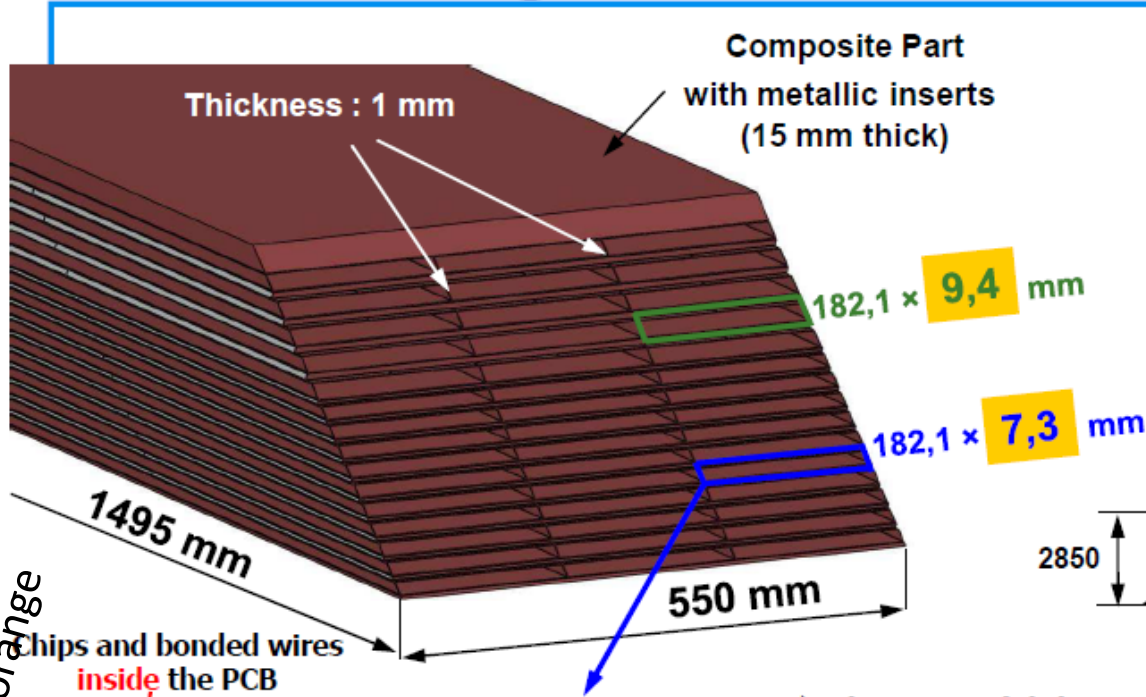


A long SLAB and a tower
 made up of short SLABs
 (30 layers)

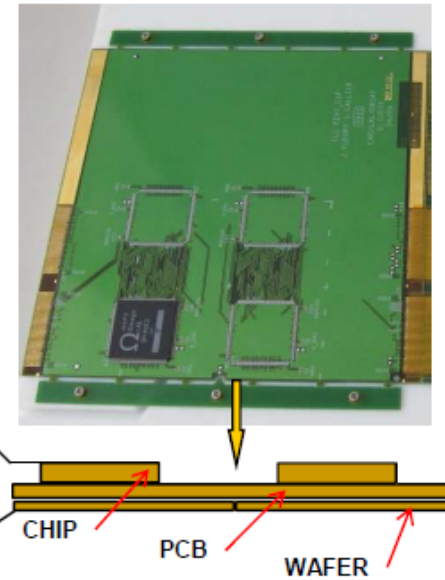
Detector design

Sandwich made up of tungsten
 PCB and silicon. Slide into a
 Composite carbon fibre structure

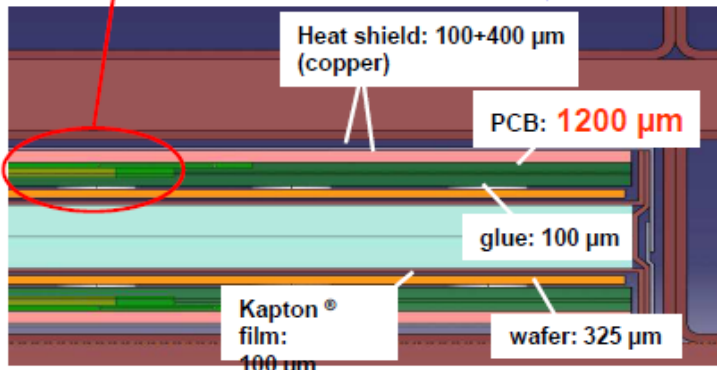
EUDET design



FEV7 CIP at the present time



Silicon wafer in orange

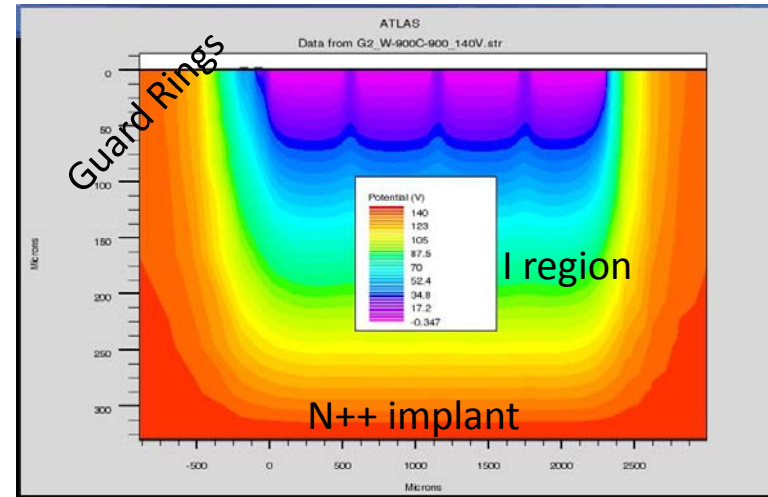


- ⇒ Clearance (slab integration) : 500 μm
- ⇒ Heat shield : 500 μm → Thermal demonstrator
- ⇒ PCB : 1200 μm → but 1100 μm used
- ⇒ Thickness of glue : 100 μm
- ⇒ Thickness of wafer : 325 μm
- ⇒ Kapton® film HV : 100 μm ? → tests
- ⇒ Thickness of W : 2100/4200 μm (± 80 μm)

Sensor Design

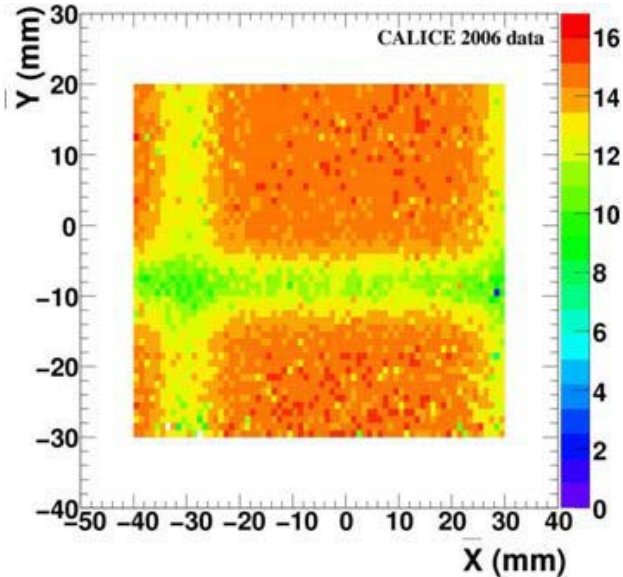
- The simplest design to control the cost
 - Few thousands of m² needed for ILD
 - Minimize the number of steps of the processing procedure
 - Guard rings = same as pixels
 - Glued on PCB : **Floating GR**
- Drawbacks : lack of optimization
 - Large dead zone at the edges: efficiency loss
 - Crosstalk between GR & pixels (Square Events)
- But...cost is still too high
 - 70 keur (including NRE) for 40 pcs of this hamamatsu prototype = 22 € / cm² (14 w/o NRE)
 - Cost limit for feasibility of ILD : ~3 € /cm²

P++ implants (pixels)



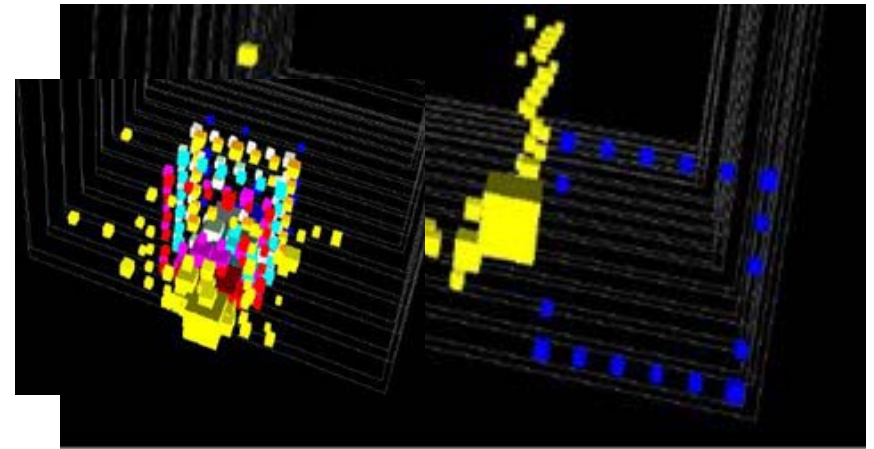
9x9 cm², 324 pixels

2 défauts



Zone “morte” à la périphérie : -20% d’efficacité de détection

Peut être compensé off-line

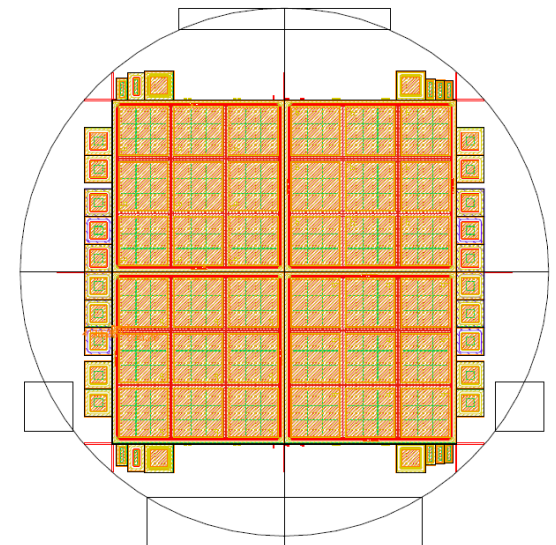
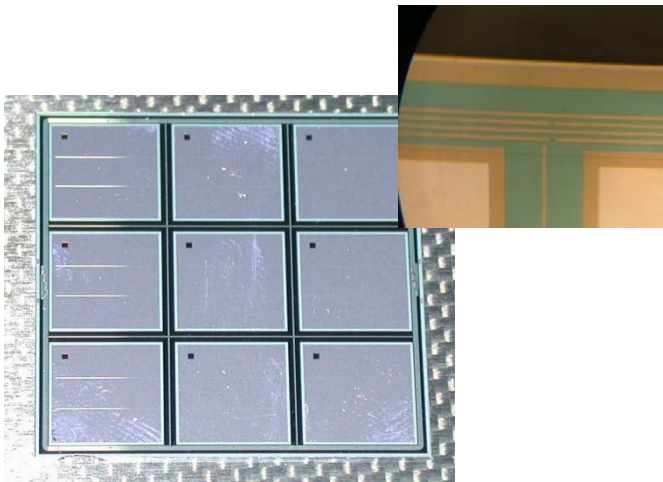
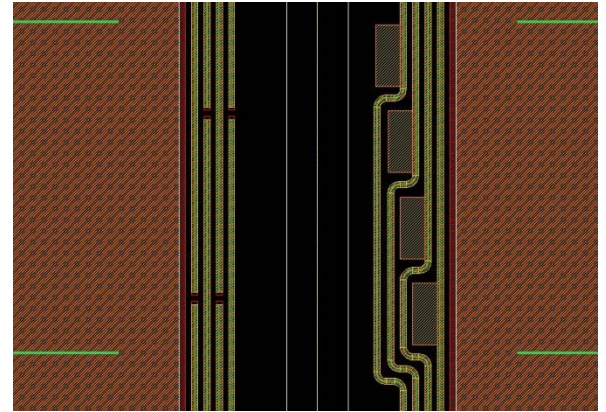


Événements carrés : diaphonie guard-rings – pixels périphériques

A minimiser par un facteur 50 à 100

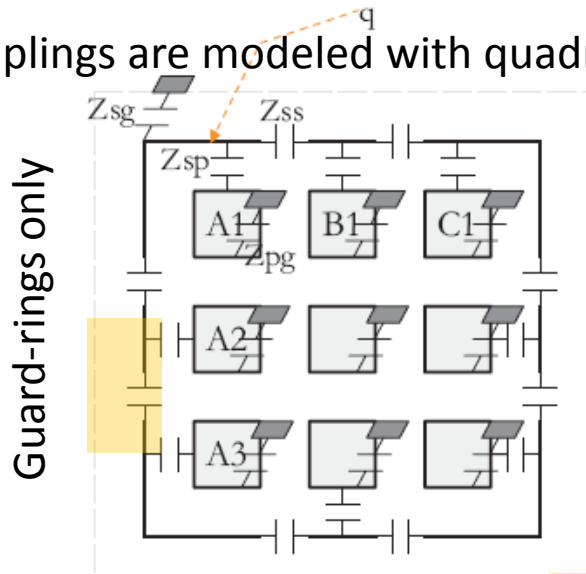
Segmented guard ring

- Should avoid the signal propagation along the border of the wafer
- Prototype wafers have been manufactured (LLR made layout)
 - OnSemi/Institute of Physics (Prague), Cz
 - BhaBha Atomic Research Centre, India
 - Tests are ongoing

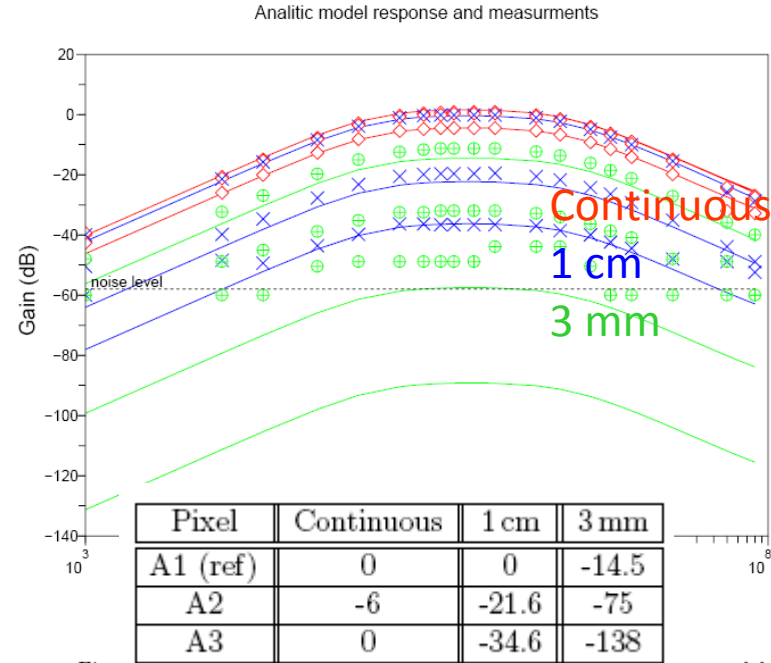


Modélisation

Couplings are modeled with quadripoles filters



Mesures :



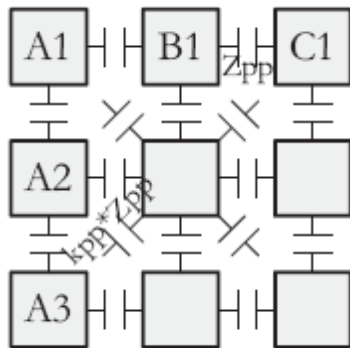
Figur

are model

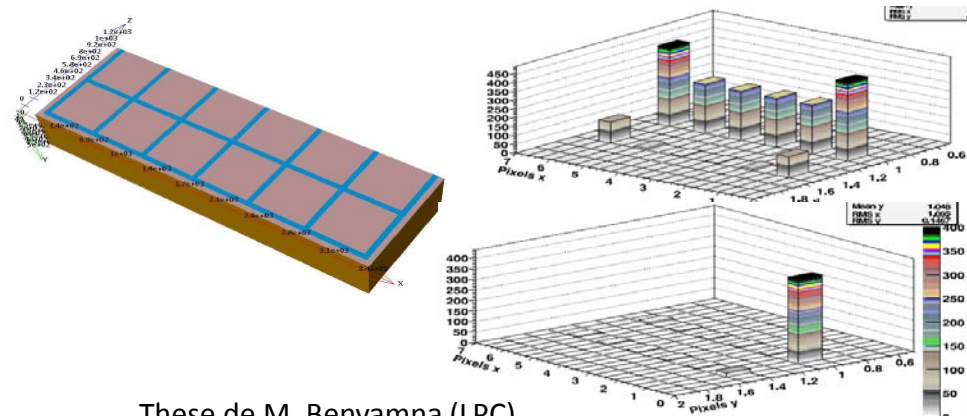
$$T = T_{elec} \times T_{pix} \times (T_{seg} \times T_{ss})^{N_{seg}} \times T_{seg} \times T_{inj}$$

Measurement electronics **Crosstalk** Charge injector

Additional electrical simulations (SPICE) including the pixel to pixel crosstalk

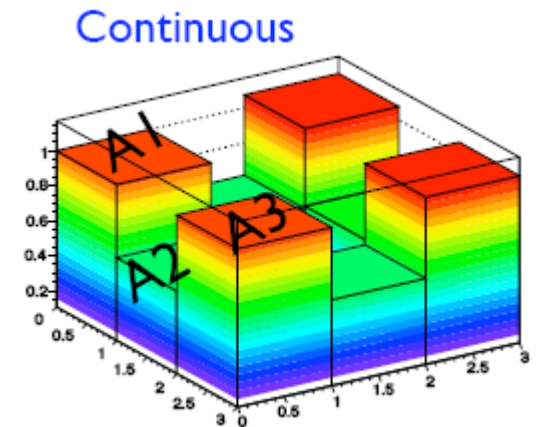
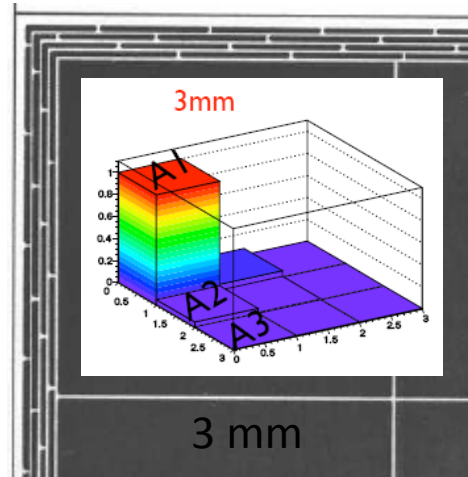
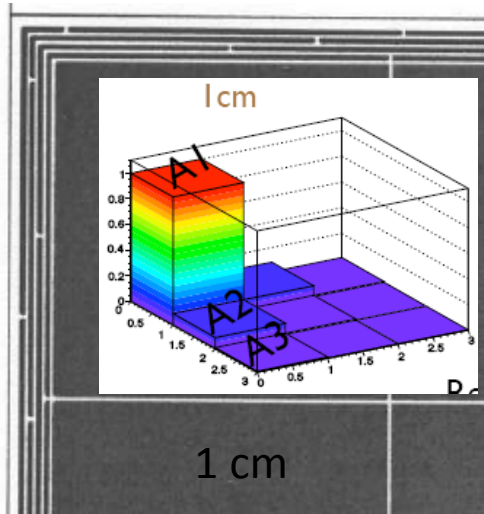
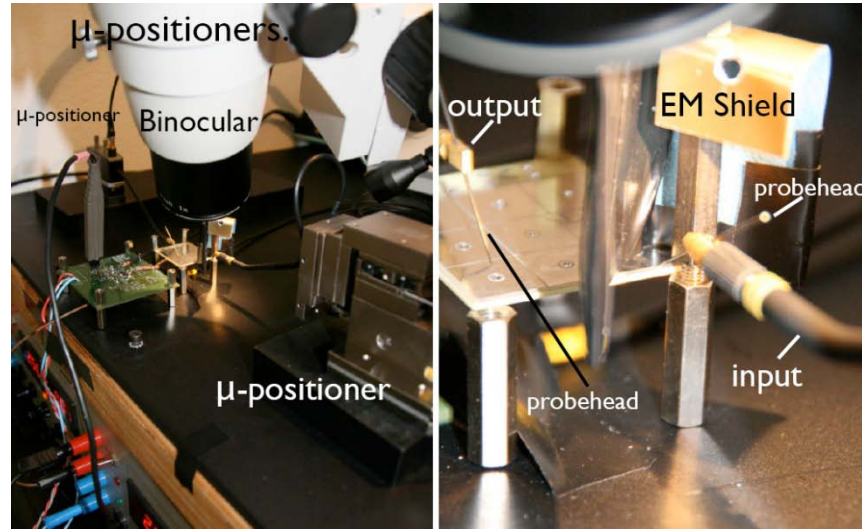


TCAD simulation (Silvaco)



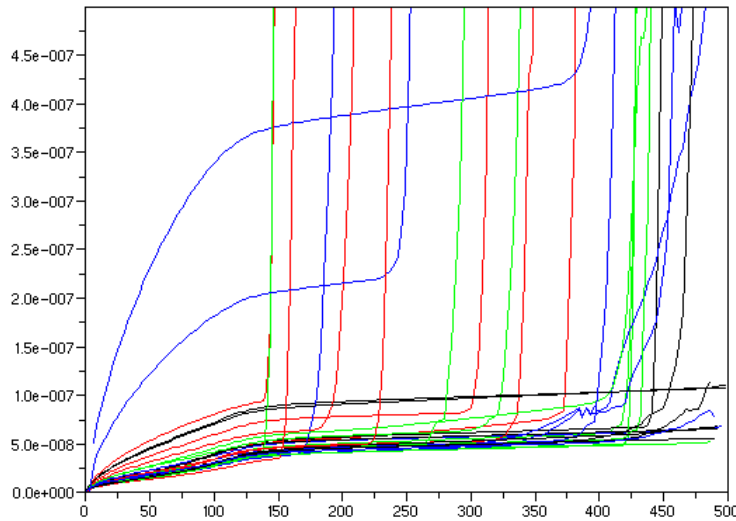
These de M. Benyamna (LPC)

Mesures



R&D on segmented guard rings

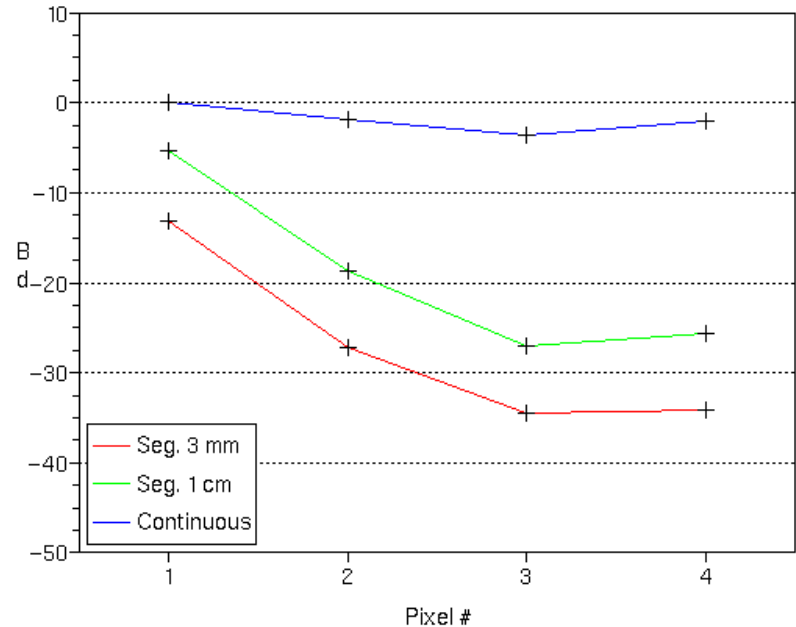
$I(V)$



Yield (Breakdown >250V)

- Continuous: 100%
- 1 cm: 85%
- 3 mm: 40%
- Mixed: 70%

Total crosstalk vs pixel number



Sum of GRs contribution
Xtalk lowered by a factor 50 (with 3 mm segments (measurements made at LPC))

Conclusion

Collaboration LLR-LPC-BARC-ONSemi

Résultats très dépendants de la techno.
Difficulté d'accès aux paramètres

Utilisation d'outils variés

CAO, TCAD, Physique, Calcul numérique
Couplage CAO-TCAD (silvaco) à étudier

Si-W ECAL (LAL, LLR, LPSC)

Prototype technologique en préparation (chips ROC, FEVx)
ILC / CLIC
ALICE et PHENIX

DAQ

Ethernet de 10M à 1G (FPGA)
TFC, SC, DAQ sur le meme lien